

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	422	"438"/\$.ccls. and (substrate wafer carrier board) with (groove cavit\$3 indentation) same (polish\$3 grind\$3) and (stack\$3 mount\$3)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L22	573	"438"/\$.ccls. and (substrate wafer carrier board) with (groove cavit\$3 indentation) same thin\$4 and (stack\$3 mount\$3)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L23	60	"438"/\$.ccls. and (substrate wafer carrier board) with (groove cavit\$3 indentation) same thinning and (stack\$3 mount\$3)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L24	510	"257"/\$.ccls. and (substrate wafer carrier board) with (groove cavit\$3 indentation) same (polish\$3 grind\$3 thinning) and (stack\$3 mount\$3)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
5	BRS	L25	79	"29"/\$.ccls. and (substrate wafer carrier board) with (groove cavit\$3 indentation) same (polish\$3 grind\$3 thinning) and (stack\$3 mount\$3)	USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
6	BRS	L26	18	"174"/\$.ccls. and (substrate wafer carrier board) with (groove cavit\$3 indentation) same (polish\$3 grind\$3 thinning) and (stack\$3 mount\$3)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L27	33	"361"/\$.ccls. and (substrate wafer carrier board) with (groove cavit\$3 indentation) same (polish\$3 grind\$3 thinning) and (stack\$3 mount\$3)	USPAT; EPO; JPO; DERWEN T; IBM_TD B